

800V 1.8Ω Super Junction Power MOSFET

Description

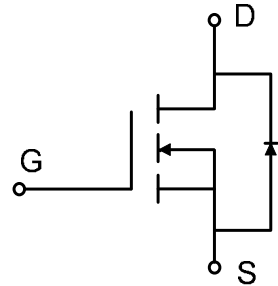
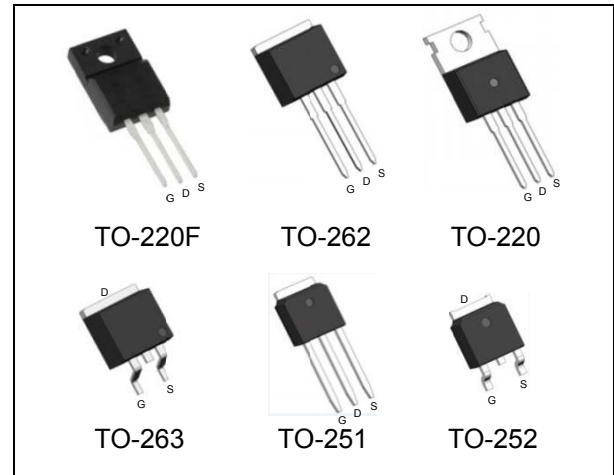
WMOS™ M3 is Wayon's 3rd generation 800V super junction MOSFET family that is utilizing charge balance technology for extremely low on-resistance and low gate charge performance. WMOS™ M3 is suitable for applications which require superior power density and outstanding efficiency.

Features

- $V_{DS} = 850V @ T_{j,max}$
- Typ. $R_{DS(on)} = 1.8\Omega$
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

LED Lighting, Charger, Adapter, PC, LCD TV, Server



Absolute Maximum Ratings

Parameter	Symbol	WMN/WMM/WMO/WMP/WMK	WML	Unit
Drain-source voltage	V_{DSS}	800		V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$) ($T_C = 100^\circ C$)	I_D	5		A
		2.5		A
Pulsed drain current ²⁾	I_{DM}	14		A
Gate-source voltage	V_{GS}	± 30		V
Avalanche energy, single pulse ³⁾	E_{AS}	20		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	0.07		mJ
Avalanche current, repetitive ²⁾	I_{AR}	0.8		A
Power dissipation ($T_C = 25^\circ C$) - Derate above $25^\circ C$	P_D	50	23	W
		0.4	0.18	W/ $^\circ C$
Operating and storage temperature range	T_{j}, T_{stg}	-55 to +150		$^\circ C$
Continuous diode forward current	I_S	5		A
Diode pulse current	$I_{S,pulse}$	14		A

Thermal Characteristics

Parameter	Symbol	WMN/WMM/WMO/WMP/WMK	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	2.4	5.4	$^\circ C/W$
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	$^\circ C/W$

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0 V, I _D =0.25 mA	800	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =0.25mA	2.5	3.3	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =800 V, V _{GS} =0 V, T _J = 25°C T _J = 125°C	- -	- 10	1 -	μA
Gate leakage current, forward	I _{GSSF}	V _{GS} =30 V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, reverse	I _{GSSR}	V _{GS} =-30 V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10 V, I _D =1A T _J = 25°C	- -	 1.8	 2.0	 Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz	-	300	-	pF
Output capacitance	C _{Oss}		-	15	-	
Reverse transfer capacitance	C _{rss}		-	1.1	-	
Turn-on delay time	t _{d(on)}	V _{DD} = 300V, I _D = 1A R _G = 25Ω, V _{GS} =10V	-	22	-	ns
Rise time	t _r		-	13	-	
Turn-off delay time	t _{d(off)}		-	45	-	
Fall time	t _f		-	18	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =480 V, I _D =1A, V _{GS} =0 to 10 V	-	1.6	-	nC
Gate to drain charge	Q _{gd}		-	6.7	-	
Gate charge total	Q _g		-	10.7	-	
Gate plateau voltage	V _{plateau}		-	5.2	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =1A	-	-	1.2	V
Reverse recovery time	t _{rr}	V _R =50 V, I _F =1A, dI _F /dt=100 A/μs	-	190	-	ns
Reverse recovery charge	Q _{rr}		-	0.65	-	μC
Peak reverse recovery current	I _{rrm}		-	6	-	A

Notes:

- Limited by $T_{j\max}$. Maximum duty cycle $D=0.5$.
- Repetitive rating: pulse width limited by maximum junction temperature
- $I_{AS}=0.8\text{ A}$, $V_{DD}=50\text{ V}$, $R_G=25\Omega$, starting $T_j=25^\circ\text{C}$

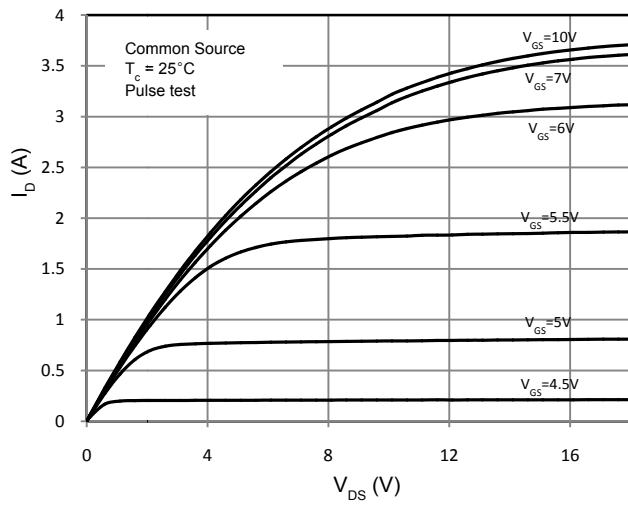


Figure 1. On-Region Characteristics

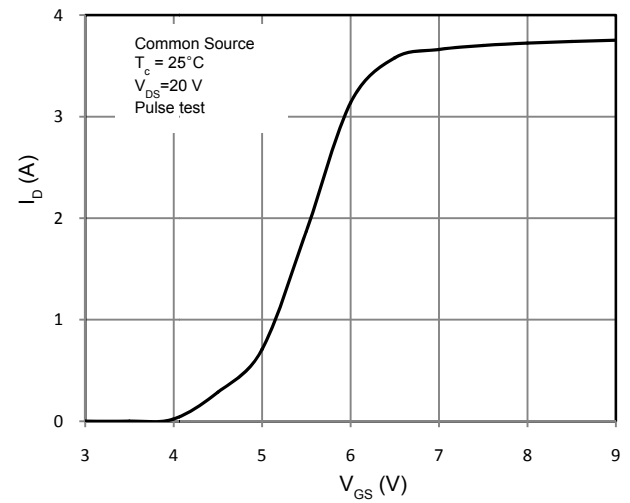


Figure 2. Transfer Characteristics

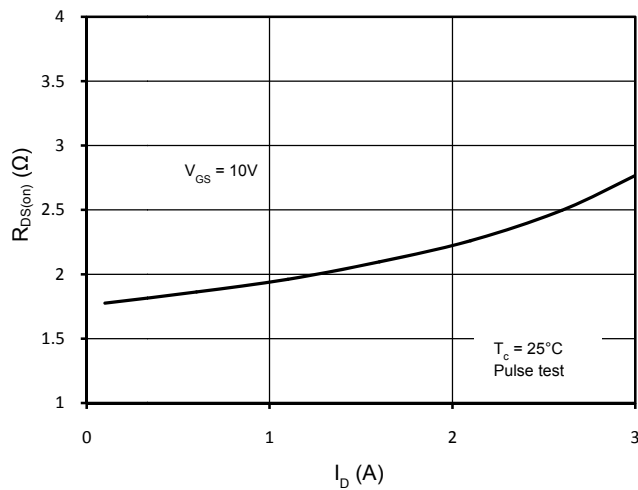


Figure 3. Static Drain-Source On Resistance

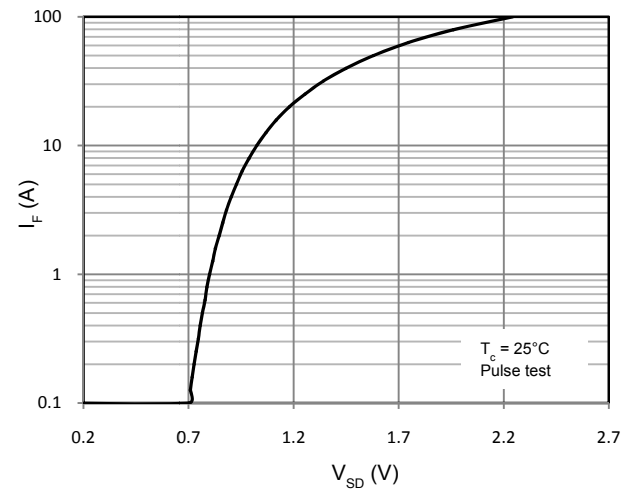
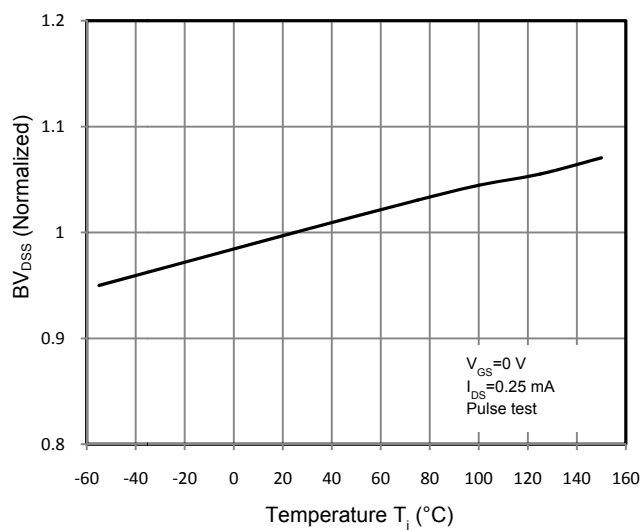
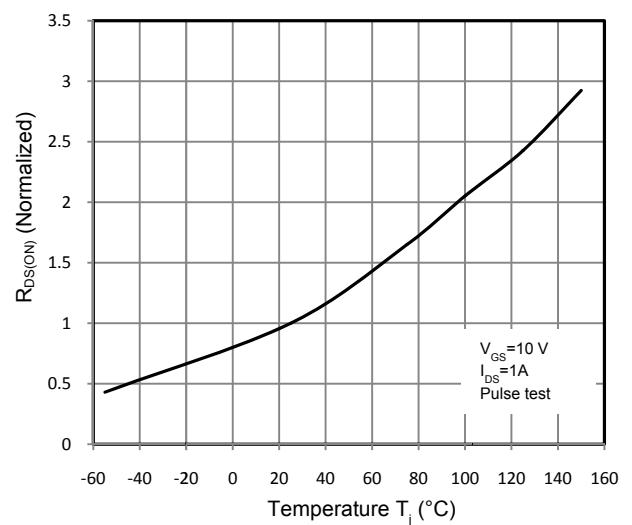


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DS} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

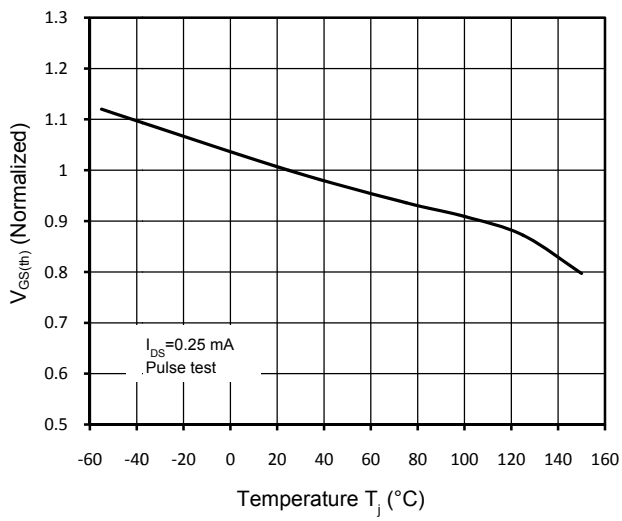


Figure 7. Threshold Voltage vs. Temperature

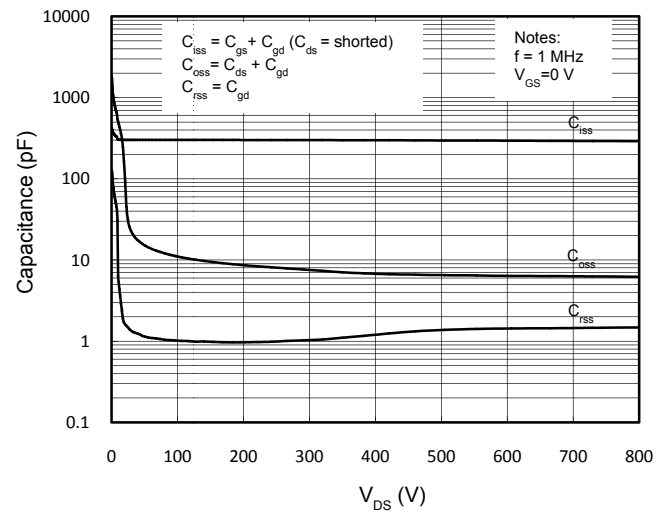


Figure 8. Capacitance Characteristics

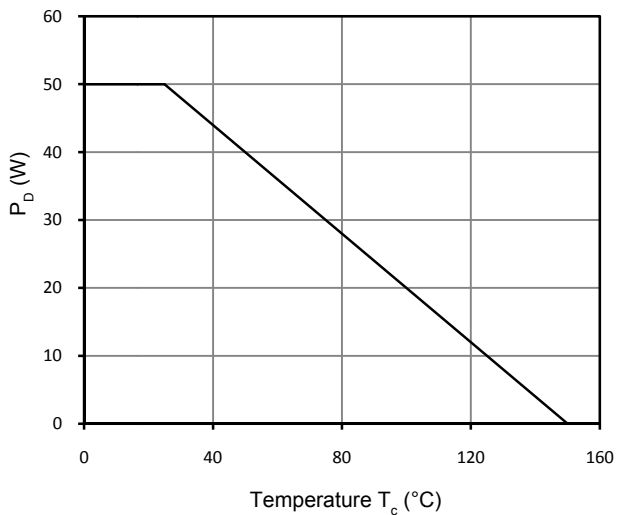


Figure 9. Power Dissipation

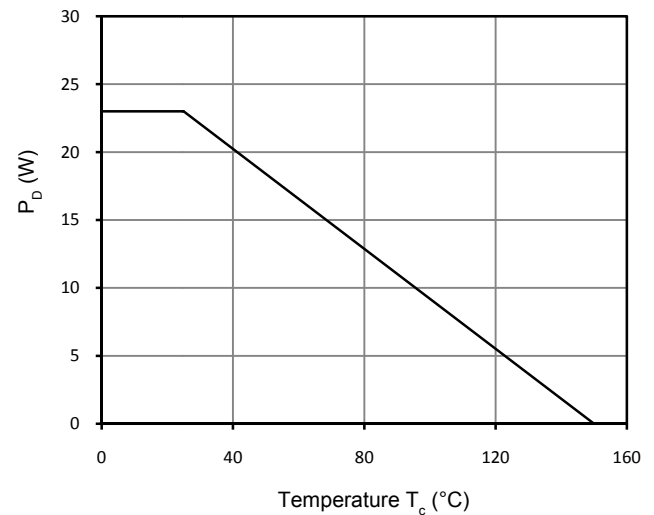


Figure 10. Power Dissipation (TO-220F)

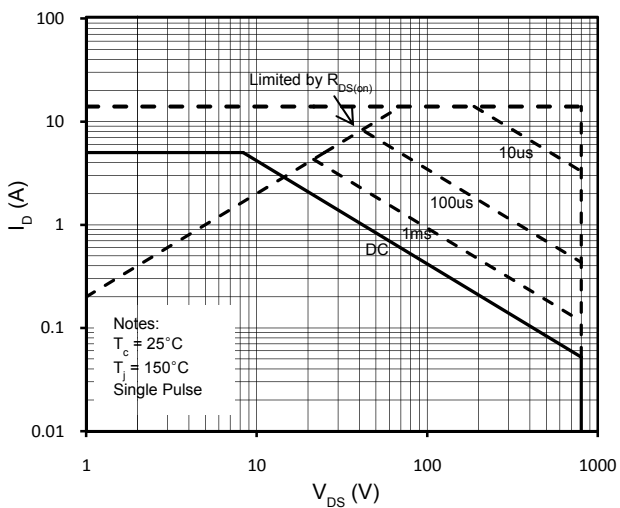


Figure 11. Maximum Safe Operating Area

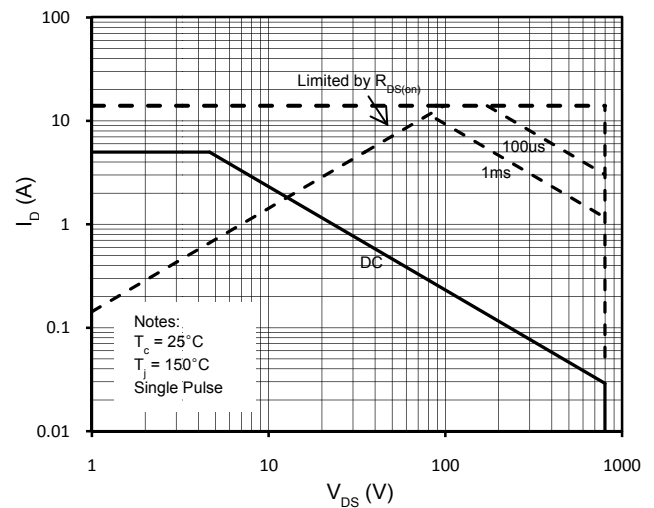


Figure 12. Maximum Safe Operating Area (TO-220F)

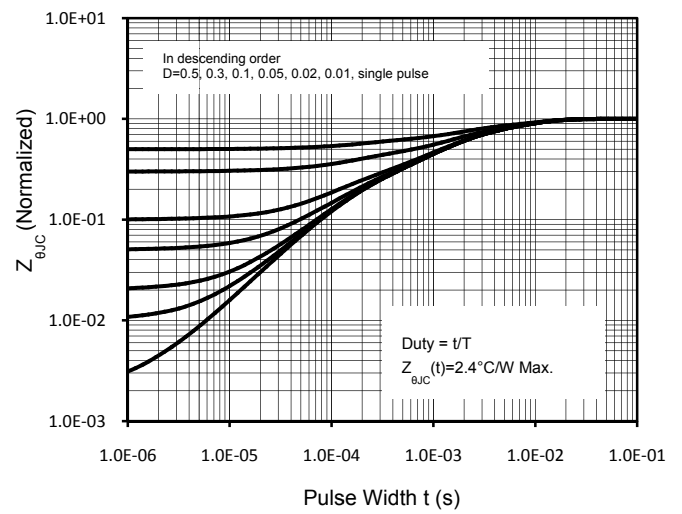
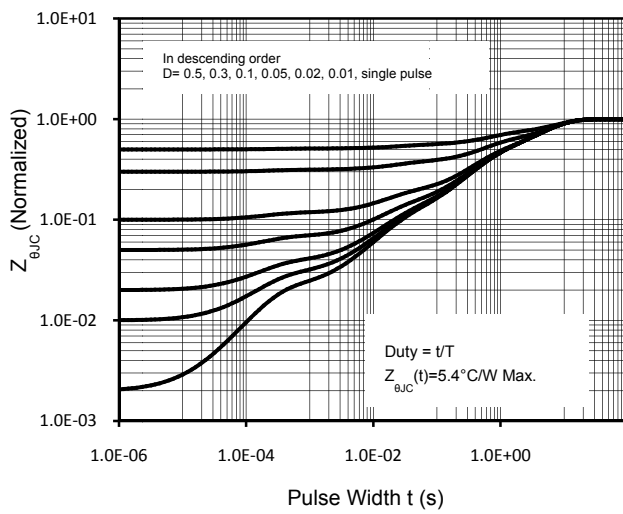


Figure 13. Transient Thermal Response Curve (TO-220F) Figure 14. Transient Thermal Response Curve

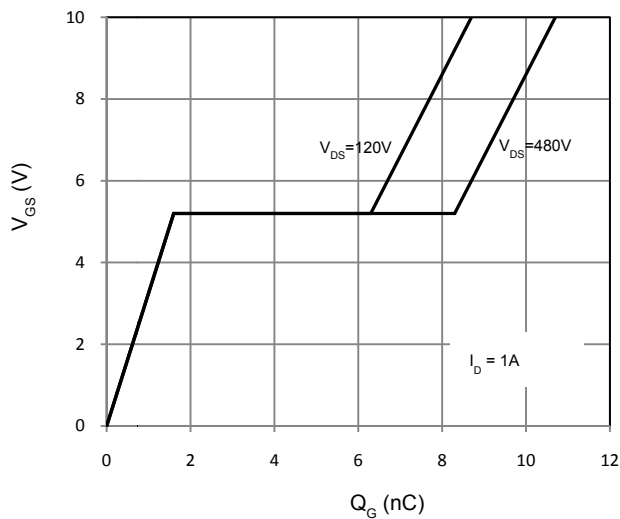
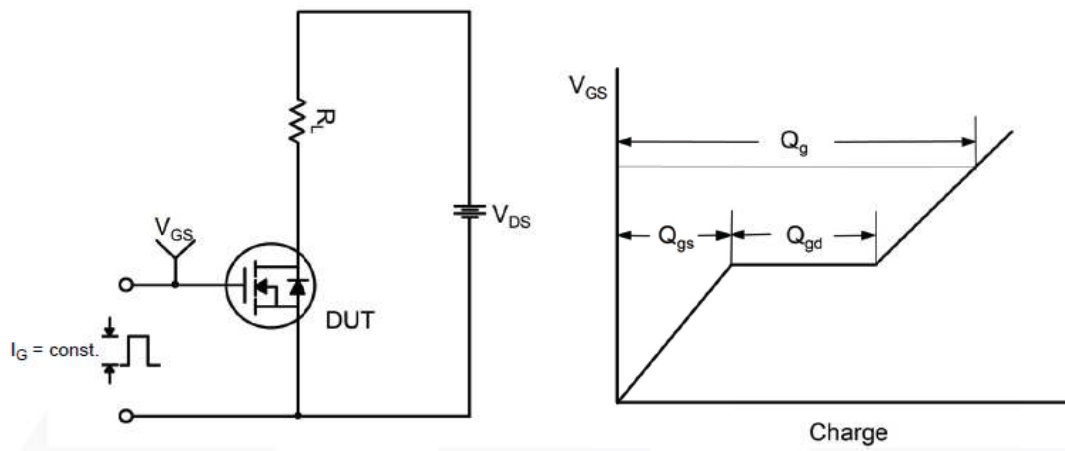
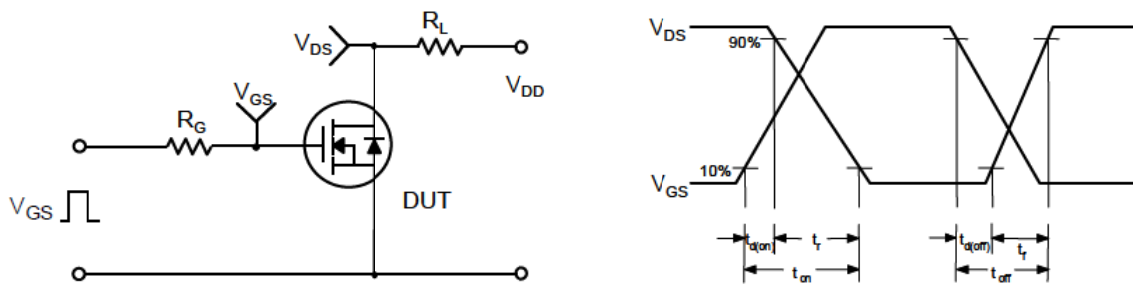


Figure 15. Gate Charge Characteristics

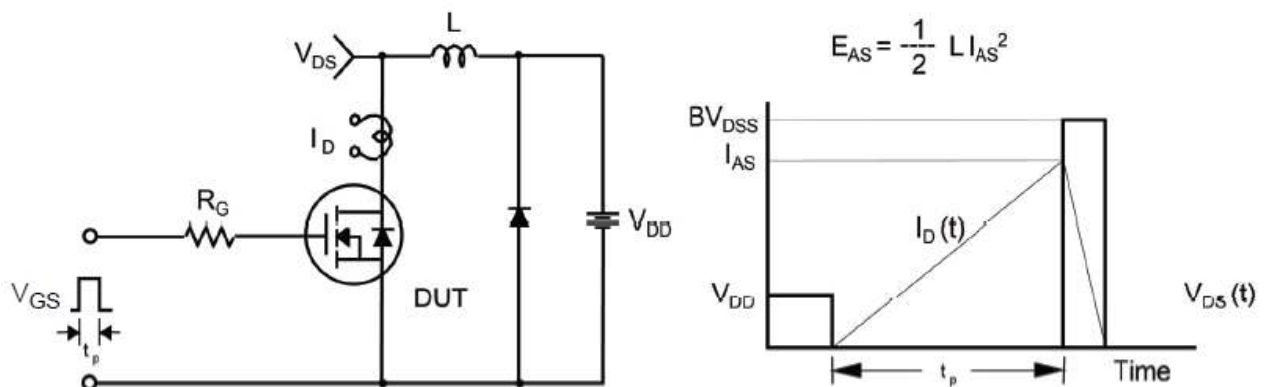
Gate Charge Test Circuit & Waveform



Switching Test Circuit & Waveforms

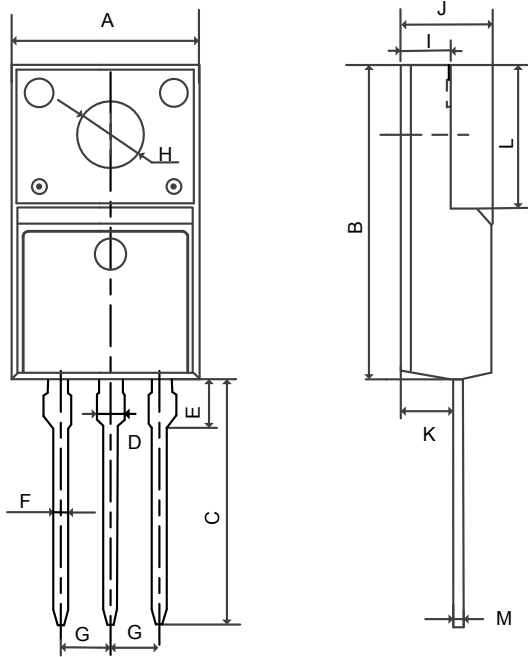


Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions for TO-220F

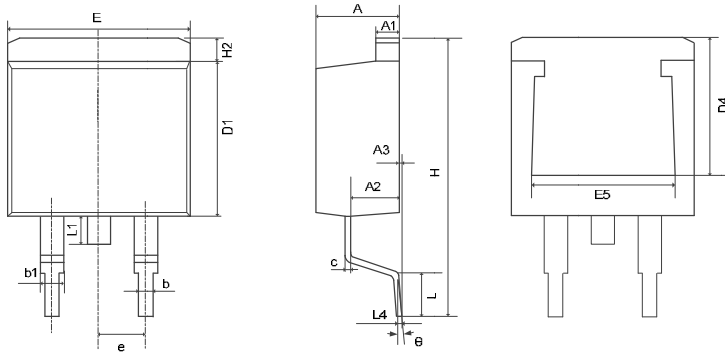
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.67	16.07
C	12.70	13.30
D	1.12	1.32
E	1.85	2.15
F	0.59	0.79
G	2.39	2.69
H	3.08	3.29
I	2.34	2.74
J	4.50	4.90
K	2.61	2.91
L	6.50	6.90
M	0.40	0.60

Mechanical Dimensions for TO-263

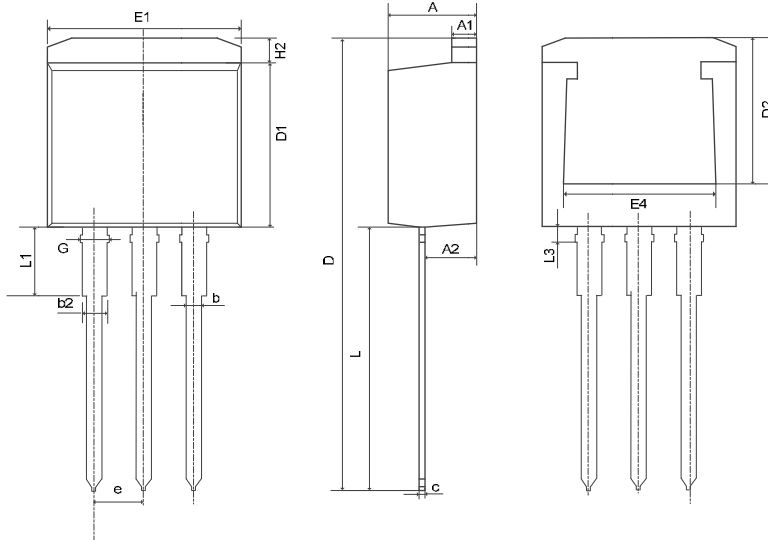
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.49	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.53
D1	8.45	8.90
D4	6.60	—
E	9.86	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	15.50
H2	1.07	1.47
L	2.00	2.70
L1	1.40	1.70
L4	0.25BSC	
θ	0°	9°

Mechanical Dimensions for TO-262

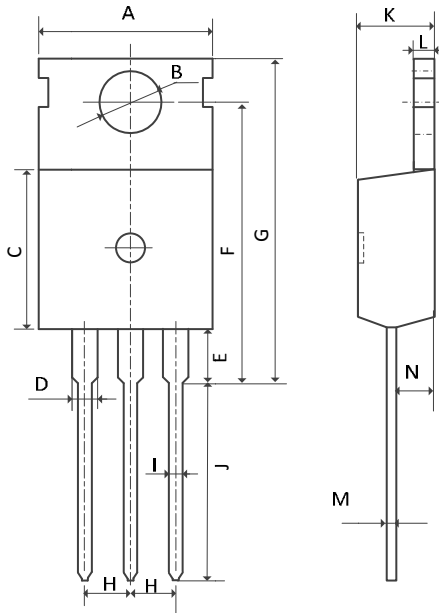
COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.49	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.53
D	23.20	24.02
D1	8.45	8.90
D2	6.00	—
E1	9.86	10.40
E4	7.06	—
e	2.54BSC	
G	1.25	1.50
H2	—	1.50
L	13.33	14.16
L1	3.50	4.00
L3	1.28	1.58

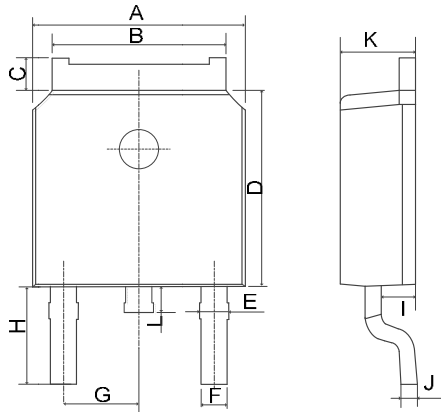
Mechanical Dimensions for TO-220

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	9.70	10.20
B	3.40	3.80
C	8.90	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

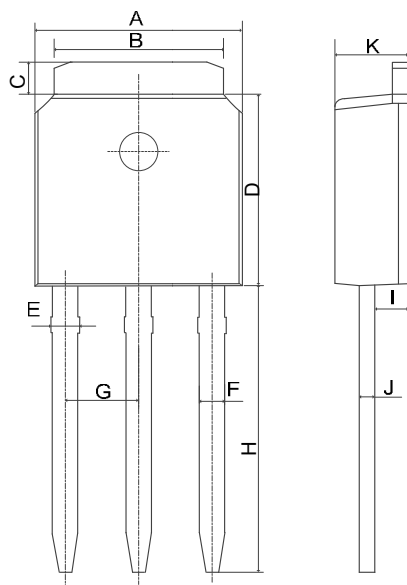
Mechanical Dimensions for TO-252



COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	2.90REF	
I	0.85	1.17
J	0.51REF	
K	2.10	2.50
L	0.40	1.00

Mechanical Dimensions for TO-251



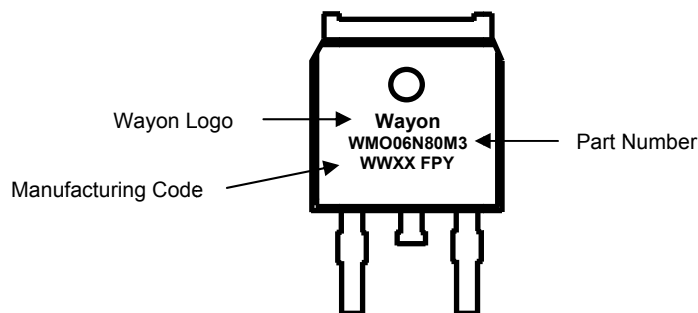
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	6.40	6.80
B	5.13	5.50
C	0.88	1.28
D	5.90	6.22
E	0.68	1.10
F	0.68	0.91
G	2.29REF	
H	9.00	9.65
I	0.85	1.17
J	0.40	0.61
K	2.10	2.50

Ordering Information

Part	Package	Marking	Packing method
WML06N80M3	TO-220F	WML06N80M3	Tube
WMM06N80M3	TO-263	WMM06N80M3	Tape and Reel
WMO06N80M3	TO-252	WMO06N80M3	Tape and Reel
WMP06N80M3	TO-251	WMP06N80M3	Tube
WMK06N80M3	TO-220	WMK06N80M3	Tube
WMN06N80M3	TO-262	WMN06N80M3	Tube

Marking Information



Contact Information

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